

Important notice

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Should be replaced with:

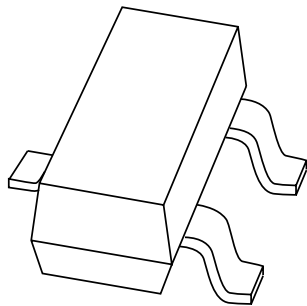
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via salesaddresses@nexperia.com). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DATA SHEET



PMBT5550 NPN high-voltage transistor

Product data sheet
Supersedes data of 1999 Apr 15

2004 Jan 21

NPN high-voltage transistor

PMBT5550

FEATURES

- Low current (max. 300 mA)
- Low voltage (max. 140 V).

APPLICATIONS

- Telephony.

DESCRIPTION

NPN high-voltage transistor in a SOT23 plastic package.
PNP complement: PMBT5401.

MARKING

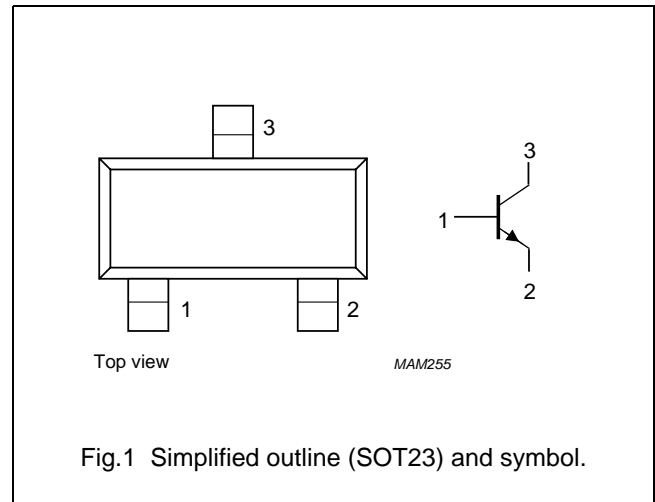
TYPE NUMBER	MARKING CODE ⁽¹⁾
PMBT5550	*1F

Note

- * = p : Made in Hong Kong.
* = t : Made in Malaysia.
* = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PMBT5550	–	plastic surface mounted package; 3 leads	SOT23

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	160	V
V_{CEO}	collector-emitter voltage	open base	–	140	V
V_{EBO}	emitter-base voltage	open collector	–	6	V
I_C	collector current (DC)		–	300	mA
I_{CM}	peak collector current		–	600	mA
I_{BM}	peak base current		–	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN high-voltage transistor

PMBT5550

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

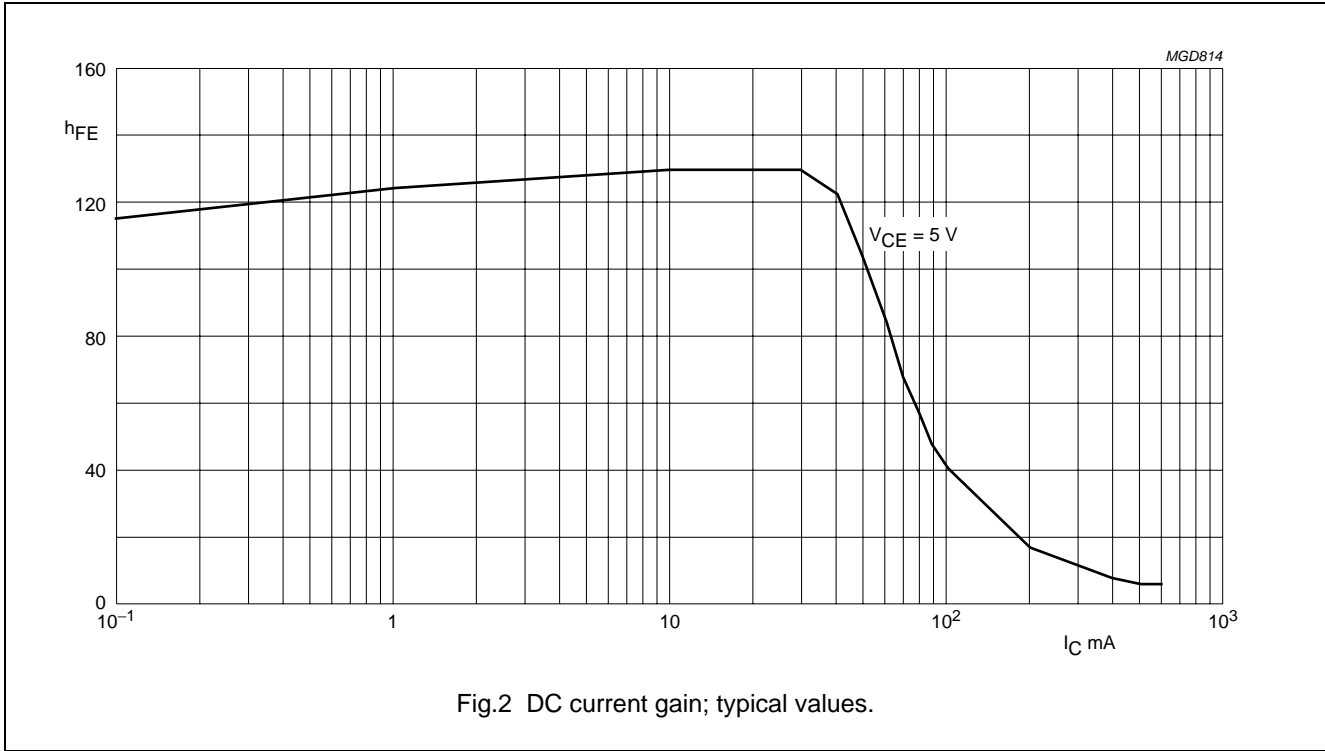
CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$I_E = 0; V_{CB} = 100\text{ V}$	–	50	nA
		$I_E = 0; V_{CB} = 100\text{ V}; T_{amb} = 100\text{ °C}$	–	50	μA
I_{EBO}	emitter-base cut-off current	$I_C = 0; V_{EB} = 4\text{ V}$	–	50	nA
h_{FE}	DC current gain	$V_{CE} = 5\text{ V};$ (see Fig.2)			
		$I_C = 1\text{ mA}$	60	–	
		$I_C = 10\text{ mA}$	60	250	
		$I_C = 50\text{ mA}$	20	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 1\text{ mA}$	–	150	mV
		$I_C = 50\text{ mA}; I_B = 5\text{ mA}$	–	250	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 1\text{ mA}$	–	1	V
		$I_C = 50\text{ mA}; I_B = 5\text{ mA}$	–	1.2	V
C_c	collector capacitance	$I_E = I_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	6	pF
C_e	emitter capacitance	$I_C = I_c = 0; V_{EB} = 0.5\text{ V}; f = 1\text{ MHz}$	–	30	pF
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	100	300	MHz
F	noise figure	$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 10\text{ Hz to }15.7\text{ kHz}$	–	10	dB

NPN high-voltage transistor

PMBT5550



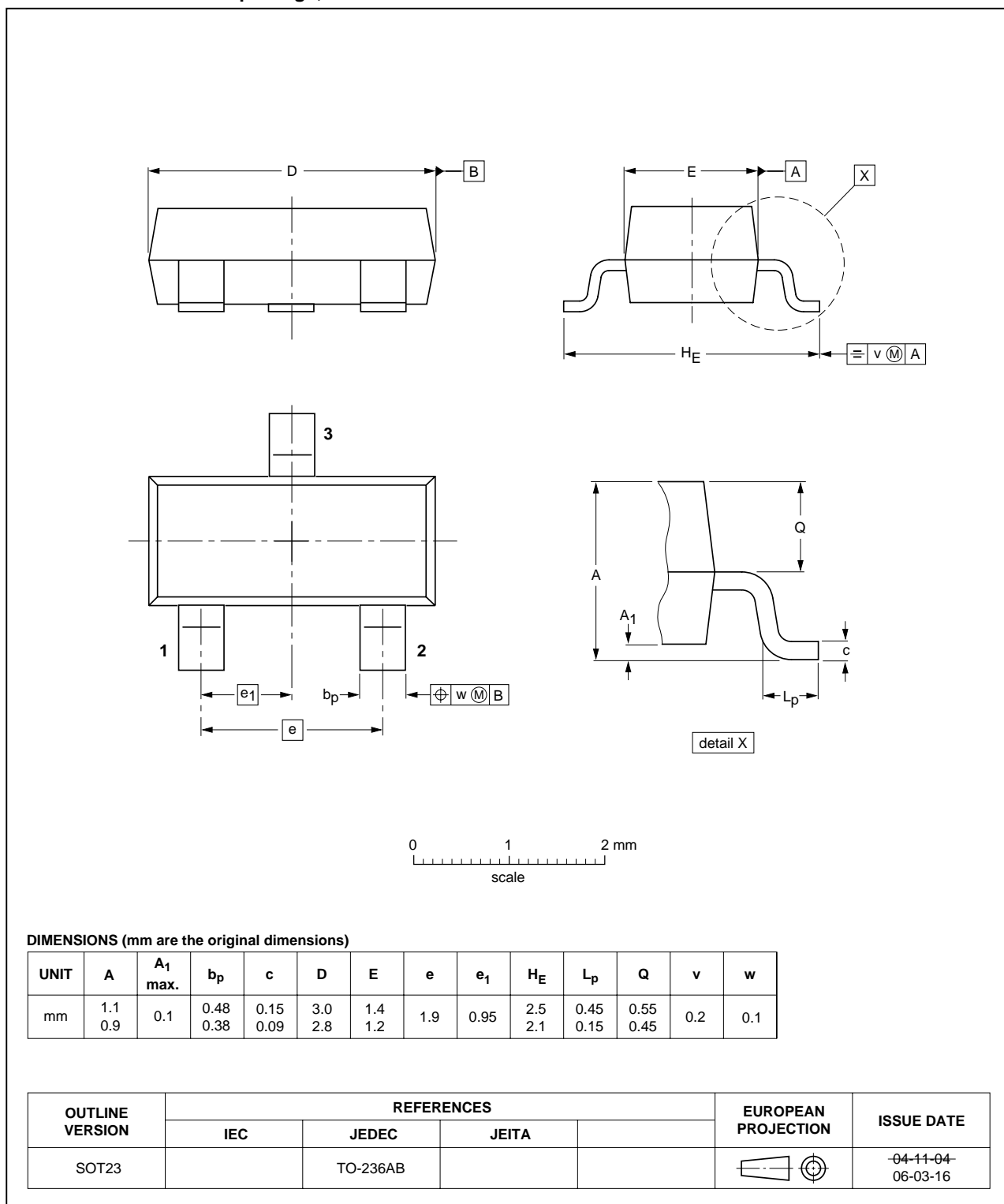
NPN high-voltage transistor

PMBT5550

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



NPN high-voltage transistor

PMBT5550

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

1. Please consult the most recently issued document before initiating or completing a design.
2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: <http://www.nxp.com>

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Printed in The Netherlands

R75/04/pp7

Date of release: 2004 Jan 21

Document order number: 9397 750 12503

